

FIG. 1

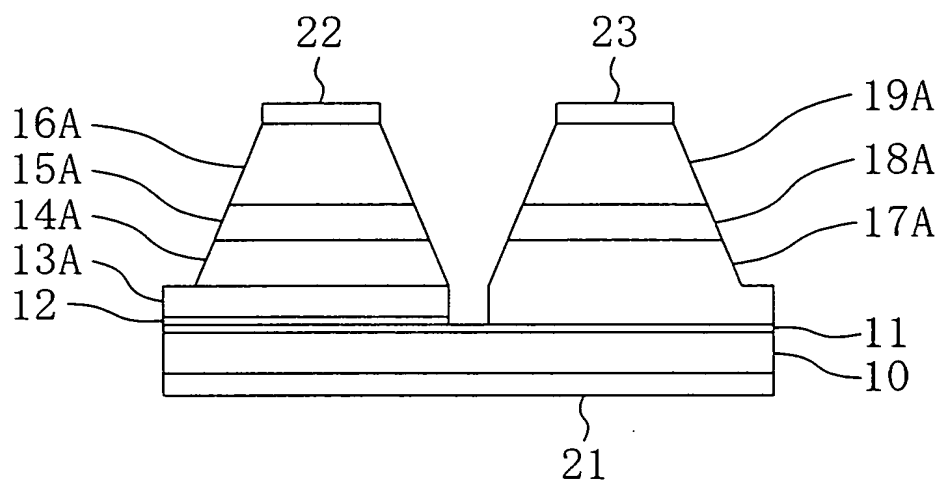
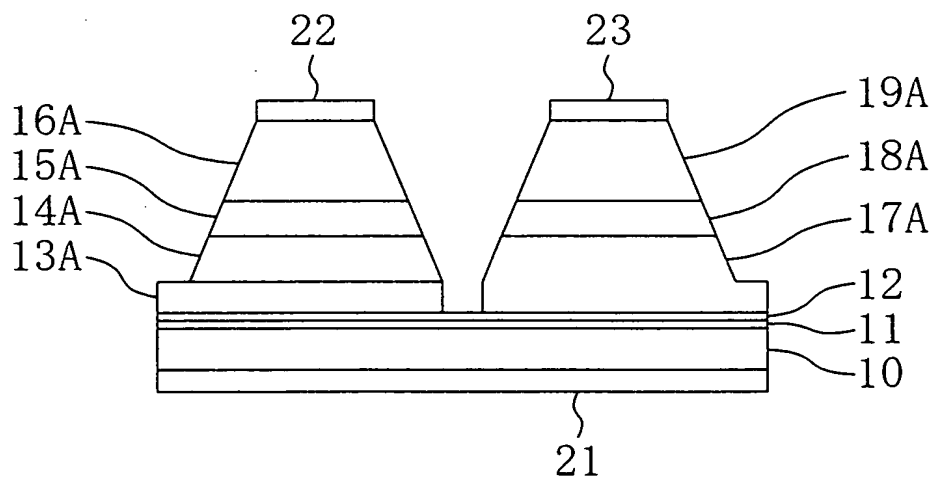
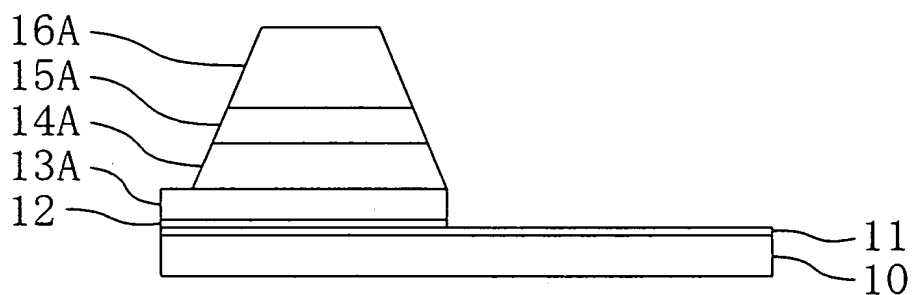


FIG. 2



A diagram showing a vertical stack of seven rectangular layers. The layers are labeled on the right side with numbers 10 through 16, from bottom to top. Layer 10 is the bottom-most layer, and layer 16 is the top-most layer. The layers are separated by thin lines, and the labels are connected to the layers by curved lines.



A cross-sectional view of a multi-layered structure. The structure consists of several horizontal layers. A central trapezoidal feature is formed by a series of nested layers. The layers are labeled on the left as 12, 13A, 14A, 15A, and 16A from bottom to top. On the right, the layers are labeled 10, 11, 17, 18, and 19 from bottom to top. The trapezoidal feature is formed by layers 12, 13A, 14A, 15A, and 16A, which are wider at the base and taper towards the top. The layers 10, 11, 17, 18, and 19 are horizontal and extend to the right, with layer 19 being the topmost layer on the right side.

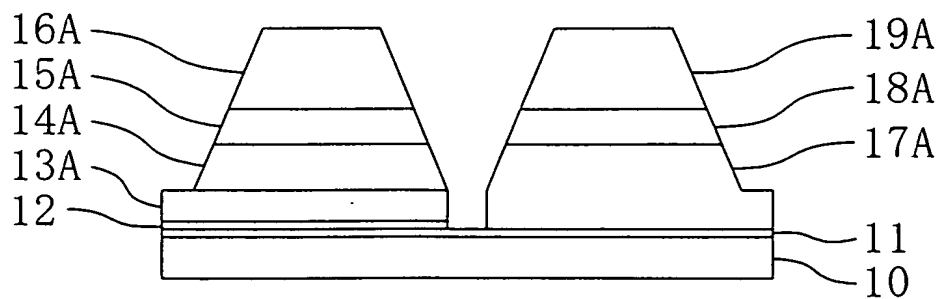
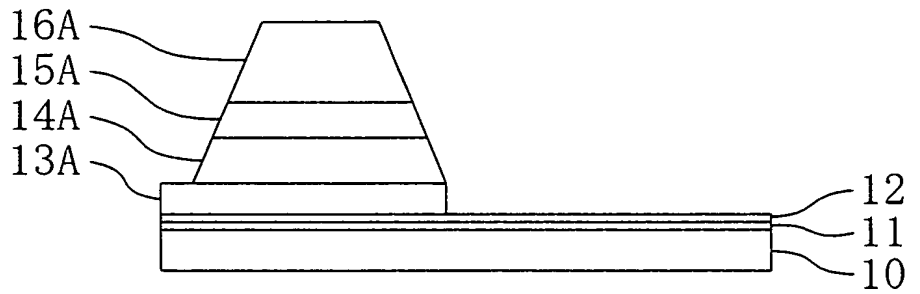


FIG. 3 (d)

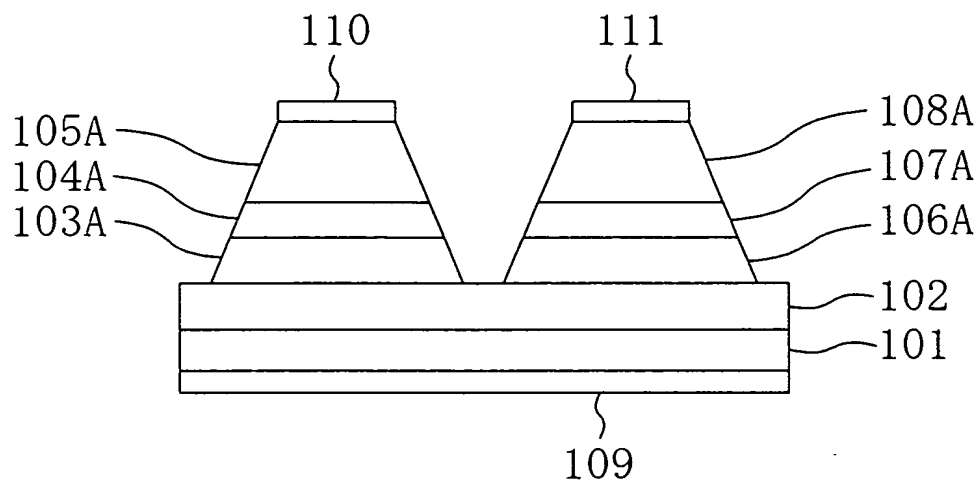
A diagram showing a cross-section of a multi-layered structure. It consists of seven horizontal layers. The layers are labeled on the right side with numbers 10 through 16, from bottom to top. Layer 10 is the bottom-most layer. Layer 11 is the second layer from the bottom. Layer 12 is the third layer from the bottom. Layer 13 is the fourth layer from the bottom. Layer 14 is the fifth layer from the bottom. Layer 15 is the sixth layer from the bottom. Layer 16 is the top-most layer. The layers are separated by thin lines, and the entire structure is enclosed in a rectangular frame.



This diagram shows a cross-sectional view of a semiconductor device. It features a substrate 10 with a thin layer 11 on top. A tapered structure 12 is formed on the substrate, consisting of multiple layers 13A, 14A, 15A, and 16A. The layers 13A, 14A, 15A, and 16A are stacked on top of each other, with the top layer 16A being the thickest. The tapered structure 12 is connected to a horizontal layer 17, which is further connected to a horizontal layer 18, and finally to a horizontal layer 19. The layers 17, 18, and 19 are stacked on top of each other, with the top layer 19 being the thickest.

A cross-sectional view of a semiconductor device. The device consists of a substrate 10 with a thin layer 11 on top. Two trapezoidal structures are formed on the substrate. Each structure has a base layer 12, followed by three horizontal layers labeled 13A, 14A, and 15A from bottom to top. The top surface of each structure is labeled 16A. The side surfaces of the structures are labeled 17A, 18A, and 19A.

FIG. 5  
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FIG. 6(a)  
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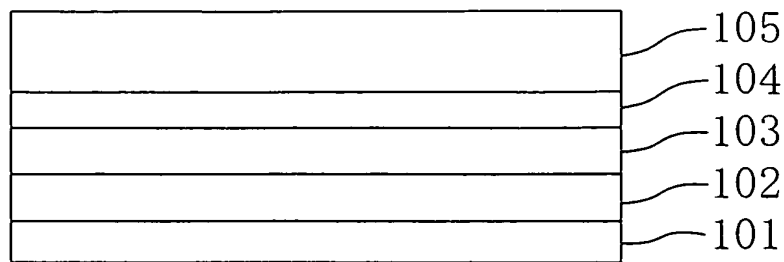


FIG. 6(b)  
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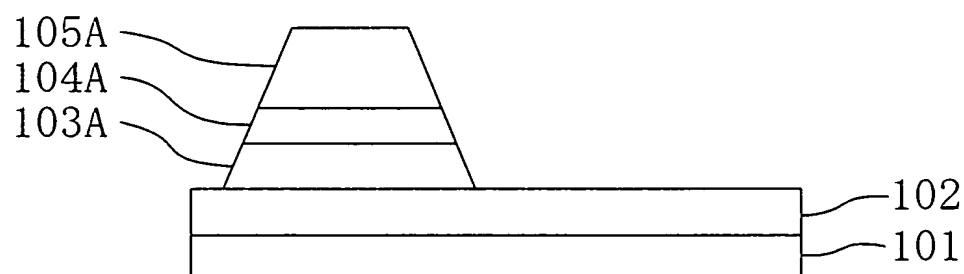


FIG. 6(c)  
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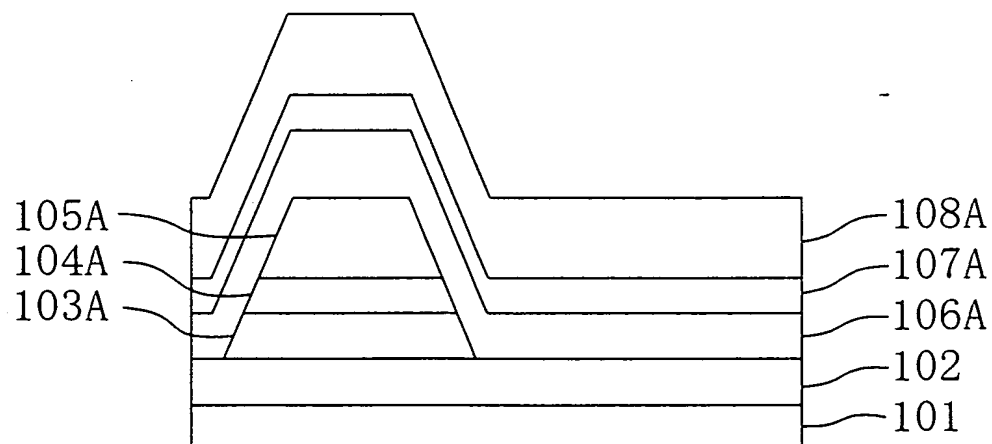


FIG. 6(d)  
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